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THIRD SERIES, VOLUME 58, NUMBER 16 ***CONTENTS*** **15 OCTOBER 1998-II**

RAPID COMMUNICATIONS

Electronic structure: wide-band, narrow-band, and strongly correlated systems

Magnetoresistance of bismuth nanowire arrays: A possible transition from one-dimensional to three-dimensional localization R10 091
J. Heremans, C. M. Thrush, Z. Zhang, X. Sun, M. S. Dresselhaus, J. Y. Ying, and D. T. Morelli

Superprism phenomena in photonic crystals R10 096
Hideo Kosaka, Takayuki Kawashima, Akihisa Tomita, Masaya Notomi, Toshiaki Tamamura, Takashi Sato, and Shojiro Kawakami

Quantum Monte Carlo simulations of infinitely strongly correlated fermions R10 100
M. Brunner and A. Muramatsu

Low-temperature specific heat of $UCu_{5-x}Pd_x$: A test for non-Fermi-liquid theory R10 104
E.-W. Scheidt, T. Schreiner, K. Heuser, S. Koerner, and G. R. Stewart

High-temperature resistivity of Sr_2RuO_4: Bad metallic transport in a good metal R10 107
A. W. Tyler, A. P. Mackenzie, S. NishiZaki, and Y. Maeno

Localization in an imaginary vector potential R10 111
P. G. Silvestrov

Probing anisotropic magnetotransport in manganese perovskites using Raman spectroscopy R10 115
H. L. Liu, S. Yoon, S. L. Cooper, S-W. Cheong, P. D. Han, and D. A. Payne

Semiconductors I: bulk

Negative-*U* centers in 4*H* silicon carbide R10 119
C. G. Hemmingsson, N. T. Son, A. Ellison, J. Zhang, and E. Janzén

Semiconductors II: surfaces, interfaces, microstructures, and related topics

Threshold behavior in the collision broadening of microcavity polaritons R10 123
C. Ciuti, V. Savona, C. Piermarocchi, A. Quattropani, and P. Schwendimann

Scanning transmission-electron microscopy study of InAs/GaAs quantum dots R10 127
P. D. Siverns, S. Malik, G. McPherson, D. Childs, C. Roberts, R. Murray, B. A. Joyce, and H. Davock

Observation of antibound states for exciton pairs by four-wave-mixing experiments in a single ZnSe quantum well R10 131
Hailong Zhou, A. V. Nurmikko, C.-C. Chu, J. Han, R. L. Gunshor, and T. Takagahara

Scattering approach to parametric pumping R10 135
P. W. Brouwer

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(Continued)

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PHYSICAL REVIEW B THIRD SERIES, VOLUME 58, NUMBER 16 15 OCTOBER 1998-II

Electronic structure of the GaAs(001)2×4 and GaAs(110) surfaces studied by high-resolution electron-energy-loss spectroscopy R10 139
F. Arciprete, F. Patella, A. Balzarotti, M. Fanfoni, N. Motta, A. Sgarlata, A. Boselli, G. Onida, A. I. Shkrebtii, and R. Del Sole

Chaotic behavior induced by point contacts in quantum dots R10 143
J. A. Vergés, E. Cuevas, M. Ortuño, and E. Louis

Polarized photoluminescence spectroscopy of single self-assembled InAs quantum dots R10 147
Y. Toda, S. Shinomori, K. Suzuki, and Y. Arakawa

Excitation transfer in self-organized asymmetric quantum-dot pairs R10 151
R. Heitz, I. Mukhametzhanov, P. Chen, and A. Madhukar

High-temperature conductance of the single-electron transistor R10 155
Georg Göppert and Hermann Grabert

Shot noise enhancement in resonant-tunneling structures in a magnetic field R10 159
V. V. Kuznetsov, E. E. Mendez, J. D. Bruno, and J. T. Pham

Ground-state wave functions of general filling factors in the lowest Landau level R10 163
J. H. Han and S.-R. Eric Yang

Possibility of p-wave pairing of composite fermions at $\nu=\frac{1}{2}$ R10 167
K. Park, V. Melik-Alaverdian, N. E. Bonesteel, and J. K. Jain

Magnons and Skyrmions in fractional Hall ferromagnets R10 171
A. H. MacDonald and J. J. Palacios

Resonant Rayleigh scattering versus incoherent luminescence in semiconductor microcavities R10 175
G. R. Hayes, S. Haacke, M. Kauer, R. P. Stanley, R. Houdré, U. Oesterle, and B. Deveaud

Optical polarization relaxation in $In_xGa_{1-x}As$-based quantum wells: Evidence of the interface symmetry-reduction effect R10 179
T. Guettler, A. L. C. Triques, L. Vervoort, R. Ferreira, Ph. Roussignol, P. Voisin, D. Rondi, and J. C. Harmand

Effect of the hole subband mixing on the spin splitting of heavy-hole excitons in coupled $In_{0.045}Ga_{0.955}As/GaAs$ double quantum wells R10 183
T. Wang, M. Bayer, and A. Forchel

Effect of electron-hole separation on the Landau-level photoluminescence in layered structures in a tilted magnetic field: Magneto-Stark effect R10 187
S. K. Lyo

Pressure dependence of optical transitions in $In_{0.15}Ga_{0.85}N/GaN$ multiple quantum wells R10 191
W. Shan, J. W. Ager III, W. Walukiewicz, E. E. Haller, M. D. McCluskey, N. M. Johnson, and D. P. Bour

Surface physics, low-dimensional systems, and related topics

Observation of an adlayer-driven substrate reconstruction in Cu-Pt(111) R10 195
B. Holst, M. Nohlen, K. Wandelt, and W. Allison

Electronic Kapitza conductance due to inelastic electron-boundary scattering R10 199
A. V. Sergeev

Ultrafast electron dynamics in gold nanoshells R10 203
R. D. Averitt, S. L. Westcott, and N. J. Halas

Surface-state contribution to the optical anisotropy of Ag(110) surfaces: A reflectance-anisotropy-spectroscopy and photoemission study R10 207
K. Stahrenberg, T. Herrmann, N. Esser, J. Sahm, W. Richter, S. V. Hoffmann, and Ph. Hofmann

Identification of electronic bonding states of hydrogen on Ni(110) R10 210
E. Boschung, Th. Pillo, J. Hayoz, L. Patthey, P. Aebi, and L. Schlapbach

(Continued)

PHYSICAL REVIEW B THIRD SERIES, VOLUME 58, NUMBER 16 15 OCTOBER 1998-II

Ripplon-induced tunneling transverse to the magnetic field R10 214
T. Barabash, M. I. Dykman, P. M. Platzman, and V. N. Smelyanskiy

ARTICLES

Electronic structure: wide-band, narrow-band, and strongly correlated systems

Picosecond time-resolved spectroscopy of the excited state in a soluble derivative of poly(phenylene vinylene): Origin of the bimolecular decay 10 218
Arthur Dogariu, Dan Vacar, and Alan J. Heeger
Friedel oscillations in the open Hubbard chain 10 225
G. Bedürftig, B. Brendel, H. Frahm, and R. M. Noack
Full-potential spin-polarized relativistic Korringa-Kohn-Rostoker method implemented and applied to bcc Fe, fcc Co, and fcc Ni 10 236
T. Huhne, C. Zecha, H. Ebert, P. H. Dederichs, and R. Zeller
Quasi-two-dimensional spin-split Fermi-liquid behavior of κ-(BEDT-TTF)$_2$I$_3$ in strong magnetic fields 10 248
N. Harrison, C. H. Mielke, D. G. Rickel, J. Wosnitza, J. S. Qualls, J. S. Brooks, E. Balthes, D. Schweitzer, I. Heinen, and W. Strunz
Comparative spectroscopic study of $NiS_{2-x}Se_x$ single crystals 10 256
J. G. Rodrigo, S. Vieira, P. Somasundaram, J. M. Honig, F. A. Chudnovsky, and V. N. Andreev
Metal-insulator transition in the one-dimensional Kondo lattice model 10 261
Karyn Le Hur
Elementary excitations in the coupled spin-orbital model 10 276
J. van den Brink, W. Stekelenburg, D. I. Khomskii, G. A. Sawatzky, and K. I. Kugel
Experimental confirmation of a p-p intraband gap in Sr_2FeO_4 ..... 10 283
G. Kh. Rozenberg, A. P. Milner, M. P. Pasternak, G. R. Hearne, and R. D. Taylor
Heavy-fermion-metal–Kondo insulator transition in $FeSi_{1-x}Al_x$ 10 288
J. F. DiTusa, K. Friemelt, E. Bucher, G. Aeppli, and A. P. Ramirez
Enhanced thermoelectric power and cooling ability near the Anderson transition 10 302
K. Durczewski and A. Krzywicki
Electronic stopping power of aluminum crystal 10 307
I. Campillo, J. M. Pitarke, and A. G. Eguiluz
Electrical and magnetic properties of a series of ternary barium metal ruthenates: $Ba_3MRu_2O_9$ (M = Fe, Co, Ni, Cu, and In) 10 315
J. T. Rijssenbeek, P. Matl, B. Batlogg, N. P. Ong, and R. J. Cava
Dipole and interfacial polarization phenomena in natural single-crystal calcite studied by the thermally stimulated depolarization currents method 10 319
N. Bogris, J. Grammatikakis, and A. N. Papathanassiou
Direct and indirect transitions in the region of the band gap using electron-energy-loss spectroscopy 10 326
B. Rafferty and L. M. Brown
Detection of inactive defects in crystalline silicon by high-resolution transmission-electron energy-loss spectroscopy 10 338
H. Kohno, T. Mabuchi, S. Takeda, M. Kohyama, M. Terauchi, and M. Tanaka
Spectral statistics in disordered metals: A trajectories approach 10 343
R. A. Smith, I. V. Lerner, and B. L. Altshuler
Signal scattering in multiport electron-waveguide devices 10 351
Jan-Olof J. Wesström

(Continued)

PHYSICAL REVIEW B **THIRD SERIES, VOLUME 58, NUMBER 16** **15 OCTOBER 1998-II**

Semiconductors I: bulk

Structure and chemical order of bulk $Si_{1-x}C_x$ amorphous alloys 10 357
Daniele Mura, Luciano Colombo, Rita Bertoncini, and Gianni Mula

Defects in electron-irradiated Si studied by positron-lifetime spectroscopy 10 363
A. Polity, F. Börner, S. Huth, S. Eichler, and R. Krause-Rehberg

Evidence of the negative-*U* behavior of H in GaAs from an investigation of H and As antisites 10 378
Aldo Amore Bonapasta

Hyperspherical adiabatic approach for excitons bound to ionized donors in semiconductors 10 383
J. J. De Groote, A. S. dos Santos, M. Masili, and J. E. Hornos

Structure and electronic properties of $FeSi_2$ 10 389
S. J. Clark, H. M. Al-Allak, S. Brand, and R. A. Abram

Band structure of BeTe: A combined experimental and theoretical study 10 394
M. Nagelstraßer, H. Dröge, H.-P. Steinrück, F. Fischer, T. Litz, A. Waag, G. Landwehr, A. Fleszar, and W. Hanke

Theoretical and experimental study of the quasistatic capacitance of metal-insulator–hydrogenated amorphous silicon structures: Strong evidence for the defect-pool model 10 401
J. P. Kleider and F. Dayoub

Role of codopant oxygen in erbium-doped silicon 10 415
Jun Wan, Ye Ling, Qiang Sun, and Xun Wang

Impact of a Jahn-Teller-like correlation coupling on the properties of mixed-valent SmB_6 ..... 10 421
O. Brandt, E. Sigmund, and M. Wagner

Quantum oscillatory properties of the semimagnetic semiconductor PbTe(Cr) 10 430
B. A. Akimov, N. A. Lvova, and L. I. Ryabova

Magnetic quenching of time-reversed light in photorefractive diluted magnetic semiconductors 10 435
M. Dinu, I. Miotkowski, and D. D. Nolte

Resonant hyper-Raman scattering in semiconductors 10 443
A. García-Cristóbal, A. Cantarero, C. Trallero-Giner, and M. Cardona

Optical-phonon behavior in $Ga_{1-x}In_xAs$: The role of microscopic strains and ionic plasmon coupling 10 452
J. Groenen, R. Carles, G. Landa, C. Guerret-Piécourt, C. Fontaine, and M. Gendry

Temperature dependence of the Raman spectrum of $Al_xGa_{1-x}As$ ternary alloys 10 463
J. Jiménez, E. Martín, A. Torres, and J. P. Landesman

Excitonic and free-carrier quantum beats created by femtosecond excitation at the band edge of GaAs 10 470
Markus Joschko, Michael Hasselbeck, Michael Woerner, Thomas Elsaesser, R. Hey, H. Kostial, and K. Ploog

Vacancies and vacancy-oxygen complexes in silicon: Positron annihilation with core electrons 10 475
J. Kuriplach, A. L. Morales, C. Dauwe, D. Segers, and M. Šob

Core x-ray spectra in semiconductors and the Mahan-Nozieres-De Dominicis model 10 484
Peteris Livins

Dispersion of the second-order nonlinear susceptibility in ZnTe, ZnSe, and ZnS 10 494
H. P. Wagner, M. Kühnelt, W. Langbein, and J. M. Hvam

Compensating levels in *p*-type ZnSe:N studied by optical deep-level transient spectroscopy 10 502
S. Q. Wang, F. Lu, Z. Q. Zhu, T. Sekiguchi, H. Okushi, K. Kimura, and T. Yao

Effects of isotope disorder on energies and lifetimes of phonons in germanium 10 510
A. Göbel, D. T. Wang, M. Cardona, L. Pintschovius, W. Reichardt, J. Kulda, N. M. Pyka, K. Itoh, and E. E. Haller

(Continued)

PHYSICAL REVIEW B **THIRD SERIES, VOLUME 58, NUMBER 16** **15 OCTOBER 1998-II**

Semiconductors II: surfaces, interfaces, microstructures, and related topics

Ordering of self-assembled $Si_{1-x}Ge_x$ islands studied by grazing incidence small-angle x-ray scattering and atomic force microscopy 10 523
M. Schmidbauer, Th. Wiebach, H. Raidt, M. Hanke, R. Köhler, and H. Wawra

Au-induced superstructure formation on vicinal Si(001) studied by low-energy electron diffraction and reflectance anisotropy spectroscopy 10 532
J. R. Power and P. Weightman

Electronic structure of the Si-rich $3C$-SiC(001)3×2 surface 10 540
H. W. Yeom, Y.-C. Chao, I. Matsuda, S. Hara, S. Yoshida, and R. I. G. Uhrberg

Ab initio calculations of soft-x-ray emission from Si(100) layers buried in GaAs 10 551
S. Mankefors, P. O. Nilsson, J. Kanski, and K. Karlsson

Electronic states in strained cleaved-edge-overgrowth quantum wires and quantum dots 10 557
M. Grundmann, O. Stier, and D. Bimberg

In-plane polarized intraband absorption in InAs/GaAs self-assembled quantum dots 10 562
S. Sauvage, P. Boucaud, J.-M. Gérard, and V. Thierry-Mieg

Exciton binding energy in a quantum well 10 568
B. Gerlach, J. Wüsthoff, M. O. Dzero, and M. A. Smondyrev

Effect of a spatially dependent effective mass on the hydrogenic impurity binding energy in a finite parabolic quantum well 10 578
Xiang-Hong Qi, Xiao-Jun Kong, and Jian-Jun Liu

Numerical study of localization in antidot lattices 10 583
Seiji Uryu and Tsuneya Ando

Screening of the surface-acoustic-wave potential by a metal gate and the quantization of the acoustoelectric current in a narrow channel 10 589
G. R. Aĭzin, Godfrey Gumbs, and M. Pepper

Conductance fluctuations in a rectangular dot at constant magnetic fields 10 597
I. V. Zozoulenko, A. S. Sachrajda, P. Zawadzki, K.-F. Berggren, Y. Feng, and Z. Wasilewski

Intrinsic admittance of unipolar double-barrier resonant-tunneling structures 10 602
A. Kindlihagen, A. G. Mal'shukov, K. A. Chao, and M. Willander

ac response of bipolar double-barrier resonant-tunneling structures 10 609
A. Kindlihagen, A. G. Mal'shukov, K. A. Chao, and M. Willander

Role of the X minimum in transport through AlAs single-barrier structures 10 619
J. J. Finley, R. J. Teissier, M. S. Skolnick, J. W. Cockburn, G. A. Roberts, R. Grey, G. Hill, M. A. Pate, and R. Planel

Magnetic-field-induced delocalization in center-doped GaAs/Al_xGa_{1-x}As multiple quantum wells 10 629
C. H. Lee, Y. H. Chang, Y. W. Suen, and H. H. Lin

Skyrmion lattice melting in the quantum Hall system 10 634
Carsten Timm, S. M. Girvin, and H. A. Fertig

Influence of magnetic-field-induced spin-density-wave motion and finite temperature on the quantum Hall effect in quasi-one-dimensional conductors: A quantum field theory 10 648
Victor M. Yakovenko and Hsi-Sheng Goan

Field theory of Skyrme lattices in quantum Hall ferromagnets 10 665
M. Abolfath and M. R. Ejtehadi

Excitonic electroabsorption spectra and Franz-Keldysh effect of $In_{0.53}Ga_{0.47}As$/InP studied by small modulation of static fields 10 674
A. Jaeger and G. Weiser

Influence of crystal-potential fluctuations on Raman spectra of coupled plasmon–LO-phonon modes in disordered systems 10 683
Yu. A. Pusep, M. T. O. Silva, J. C. Galzerani, N. T. Moshegov, and P. Basmaji

(Continued)

PHYSICAL REVIEW B THIRD SERIES, VOLUME 58, NUMBER 16 15 OCTOBER 1998-II

Exciton transport and nonradiative decay in semiconductor nanostructures 10 687
I. N. Krivorotov, T. Chang, G. D. Gilliland, L. P. Fu, K. K. Bajaj, and D. J. Wolford
Exciton photoluminescence of hexagonal ZnO 10 692
T. V. Butkhuzi, T. G. Chelidze, A. N. Georgobiani, D. L. Jashiashvili, T. G. Khulordava, and B. E. Tsekvava
Spatial distributions of near-band-gap uv and yellow emission on MOCVD grown GaN epifilms 10 696
L. W. Tu, Y. C. Lee, D. Stocker, and E. F. Schubert
Effects of interface-layers composition and strain distribution on the optical transitions of InAs quantum dots on InP 10 700
H. Folliot, S. Loualiche, B. Lambert, V. Drouot, and A. Le Corre
Optical emission of a one-dimensional electron gas in semiconductor V-shaped quantum wires 10 705
H. P. van der Meulen, J. Rubio, I. Azcona, J. M. Calleja, T. C. Rojas, S. I. Molina, R. Garcia, and U. Marti
Electric-field-dependent absorption of ZnSe-based quantum wells: The transition from two-dimensional to three-dimensional behavior 10 709
D. Merbach, E. Schöll, W. Ebeling, P. Michler, and J. Gutowski
van der Waals interaction of a molecule with a semiconductor surface not in equilibrium 10 721
Fridrikh G. Bass and Valeri Z. Lozovski
Charge exchange in an atom-surface system under laser irradiation 10 728
Andrey V. Lugovskoy
Mechanisms of cluster implantation in silicon: A molecular-dynamics study 10 736
Sigeo Ihara, Satoshi Itoh, and Jun'ichi Kitakami
Local atomic structure in strained interfaces of $In_xGa_{1-x}As/InP$ heterostructures 10 745
F. Boscherini, C. Lamberti, S. Pascarelli, C. Rigo, and S. Mobilio
Vibrational properties of Ge- and Sb-adsorbed Si(001) surfaces 10 754
H. M. Tütüncü, S. J. Jenkins, and G. P. Srivastava
Applying voltage sources to a Luttinger liquid with arbitrary transmission 10 761
Reinhold Egger and Hermann Grabert
Exciton binding energies in polar quantum wells with finite potential barriers 10 769
Ruisheng Zheng and Mitsuru Matsuura
Bulk quantum Hall effect in η-Mo_4O_{11} 10 778
S. Hill, S. Uji, M. Takashita, C. Terakura, T. Terashima, H. Aoki, J. S. Brooks, Z. Fisk, and J. Sarrao
Conductance quantization in a periodically modulated quantum channel: Backscattering and mode mixing 10 784
P. Singha Deo, B. C. Gupta, A. M. Jayannavar, and F. M. Peeters
Theory of potential modulation in lateral surface superlattices. III. Two-dimensional superlattices and arbitrary surfaces 10 789
John H. Davies, David E. Petticrew, and Andrew R. Long

Surface physics, low-dimensional systems, and related topics

In situ x-ray standing-wave analysis of electrodeposited Cu monolayers on GaAs(001) 10 800
G. Scherb, A. Kazimirov, J. Zegenhagen, T. L. Lee, M. J. Bedzyk, H. Noguchi, and K. Uosaki
LEED holography applied to a complex superstructure: A direct view of the adatom cluster on SiC(111)-(3×3) 10 806
K. Reuter, J. Schardt, J. Bernhardt, H. Wedler, U. Starke, and K. Heinz
Role of scattering-factor anisotropy in electron, positron, and photon holography 10 815
S. Y. Tong, C. W. Mok, Huasheng Wu, and L. Z. Xin
Light emission from a scanning tunneling microscope: Fully retarded calculation 10 823
Peter Johansson
Surface-tip interactions in noncontact atomic-force microscopy on reactive surfaces: Si(111) 10 835
Rubén Pérez, Ivan Štich, Michael C. Payne, and Kiyoyuki Terakura

(Continued)

PHYSICAL REVIEW B THIRD SERIES, VOLUME 58, NUMBER 16 15 OCTOBER 1998-II

Molecular and intramolecular dynamics of a C_{80} dimetallofullerene 10 850
Wataru Sato, Keisuke Sueki, Koichi Kikuchi, Shinzo Suzuki, Yohji Achiba, Hiromichi Nakahara, Yoshitaka Ohkubo, Kichizo Asai, and Fumitoshi Ambe

Ab initio calculations of the structural properties of the YSi_2 (0001) surface 10 857
L. Magaud, A. Pasturel, G. Kresse, and J. Hafner

Molecular orientation determined by second-harmonic generation: Self-assembled monolayers 10 860
Frank Eisert, Oliver Dannenberger, and Manfred Buck

Alloy decomposition during growth due to mobility differences 10 871
P. Venezuela and J. Tersoff

Control of heteroepitaxial stacking by substrate miscut 10 875
S. W. Bonham and C. P. Flynn

Molecular orientation with visible light: Reflectance-anisotropy spectroscopy of 3-thiophene carboxylate on Cu(110) surfaces 10 883
B. G. Frederick, R. J. Cole, J. R. Power, C. C. Perry, Q. Chen, N. V. Richardson, P. Weightman, C. Verdozzi, D. R. Jennison, P. A. Schultz, and M. P. Sears

Adsorption energies and ordered structures of hydrogen on Pd(111) from density-functional periodic calculations 10 890
O. M. Løvvik and R. A. Olsen

Elastic scattering of surface plasmon polaritons: Modeling and experiment 10 899
Sergey I. Bozhevolnyi and Victor Coello

Theoretical study of electrical conduction through a molecule connected to metallic nanocontacts 10 911
Eldon G. Emberly and George Kirczenow

Electromagnetic response of charged bosons coupled to a Chern-Simons gauge field: A path-integral approach 10 921
D. G. Barci, E. V. Corrêa Silva, and J. F. Medeiros Neto

Electronic transport by ultrathin molybdenum layers buried in amorphous silicon 10 933
H.-M. Latuske and T. P. Drüsedau

Tunneling in multilayer fullerene/Al_2O_3 and fullerene/Ge systems 10 942
S. Nolen and S. T. Ruggiero

Femtosecond photoemission study of ultrafast electron dynamics in single-crystal Au(111) films 10 948
J. Cao, Y. Gao, H. E. Elsayed-Ali, R. J. D. Miller, and D. A. Mantell

Ion neutralization on composite catalysts 10 953
Y. G. Weng, Z. X. Yang, G. H. Wei, X. Q. Dai, S. Y. Wei, and T. Zhang

Positive- and negative-ion formation in low-energy O^+-Cu(001) scattering 10 959
C. A. Keller, A. C. Lavery, and B. H. Cooper

Experimental analysis of valence-band photoemission intensities for Cu(111) and Cu(100) 10 969
A. Gerlach, R. Matzdorf, and A. Goldmann

Reliable determination of kinetics parameters of adatoms in thin-film epitaxy 10 975
X. D. Zhu

Laser interaction with Br-GaAs(110): Etching and atomic desorption 10 981
B. Y. Han and J. H. Weaver

Arsenic redistribution at the SiO_2/Si interface during oxidation of implanted silicon 10 990
Fabio Iacona, Vito Raineri, Francesco La Via, Antonio Terrasi, and Emanuele Rimini

Bond-charge-model calculation of vibrational properties in small carbon aggregates: From spherical clusters to linear chains 11 000
Nicola Breda, Giovanni Onida, Giorgio Benedek, Gianluca Colò, and Ricardo A. Broglia

Optimized geometries and electronic structures of graphyne and its family 11 009
Nobuo Narita, Sumiaki Nagai, Shugo Suzuki, and Kenji Nakao

Cation intercalation in sputter-deposited W oxide films 11 015
Maria Strømme Mattsson

(Continued)

PHYSICAL REVIEW B **THIRD SERIES, VOLUME 58, NUMBER 16** **15 OCTOBER 1998-II**

Correlation and electron-phonon effects in the valence-band photoemission spectra of single-phase K_3C_{60} films 11 023
A. Goldoni, S. L. Friedmann, Z.-X. Shen, and F. Parmigiani
Ethylene on Si(001)-2×1 and Si(111)-7×7: X-ray photoemission spectroscopy with synchrotron radiation 11 029
François Rochet, Florence Jolly, Fabrice Bournel, Georges Dufour, Fausto Sirotti, and Jean-Louis Cantin
Ab initio adiabatic He and Ne interaction on Ag: An all-electron calculation 11 043
M. I. Trioni, S. Marcotulio, G. Santoro, V. Bortolani, G. Palumbo, and G. P. Brivio

COMMENTS

Comment on ''Quaternary alloy $Zn_{1-x}Mg_xS_ySe_{1-y}$'' 11 052
U. Lunz, C. R. Becker, W. Faschinger, and G. Landwehr
Reply to ''Comment on 'Quaternary alloy $Zn_{1-x}Mg_xS_ySe_{1-y}$' '' 11 054
Hiroyuki Okuyama and Akira Ishibashi

Cumulative Author Index 11 055